



01.08.28

◆ Features

- Low voltage of +3.3 V single power supply
- $6.5 \text{ k}\Omega$ high transimpedance
- Typical 320 MHz broad bandwidth
- 27 dB high gain
- 0 dBm large optical input
- Over 30 dB wide dynamic range
- Differential output

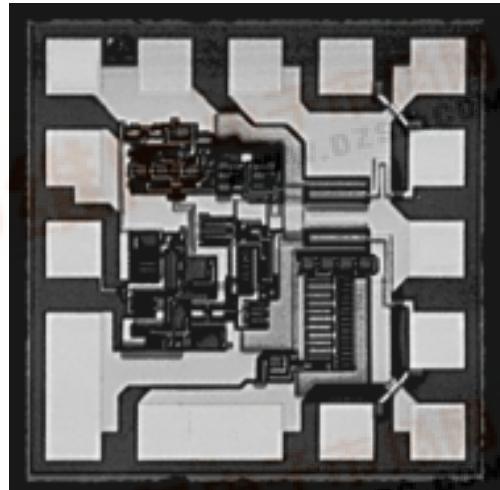
◆ Applications

- Preamplifier of an optical receiver circuit for OC-12/STM-4 (622 Mb/s)

F0100208B

3.3 V / 622 Mb/s Receiver

Transimpedance Amplifier



◆ Functional Description

The F0100208B is a stable GaAs integrated transimpedance amplifier capable of 27 dB gain at a typical 320 MHz 3 dB-cutoff-frequency, making it ideally suited for a 622 Mb/s optical receiver circuit, for example, OC-12/STM-4, instrumentation, and measurement applications. The integrated feedback loop design provides broad bandwidth and stable operation. The F0100208B typically specifies a high transimpedance of $6.5 \text{ k}\Omega$ ($R_s=RL=50\Omega$) with a wide dynamic range of over 30 dB. It also provides a large optical input overload of more than 0 dBm. Furthermore, it can operate with a low supply voltage of single +3.3 V. It features a typical dissipation current of 25 mA.

Only chip-shipment is available for all product lineups of GaAs transimpedance amplifiers, because the packaged preamplifier can not operate with the maximum performance owing to parasitic capacitance of the package.

◆ Absolute Maximum Ratings

$T_a=25^\circ\text{C}$, unless specified

Parameter	Symbol	Value	Units
Supply Voltage	V_{DD}	$V_{SS}-0.5$ to $V_{SS}+4.0$	V
Supply Current	I_{DD}	50	mA
Ambient Operating Temperature	T_a	-40 to +90	$^\circ\text{C}$
Storage Temperature	T_{stg}	-50 to +125	$^\circ\text{C}$

◆ Recommended Operating Conditions

$T_a=25^\circ\text{C}$, $V_{DD}=+3.3\text{ V}$, $V_{SS}=\text{GND}$, unless specified

Parameter	Symbol	Value		Units
		Min.	Max.	
Supply Voltage	V_{DD}	2.9	3.6	V
Ambient Operating Temperature	T_a	0	85	$^\circ\text{C}$

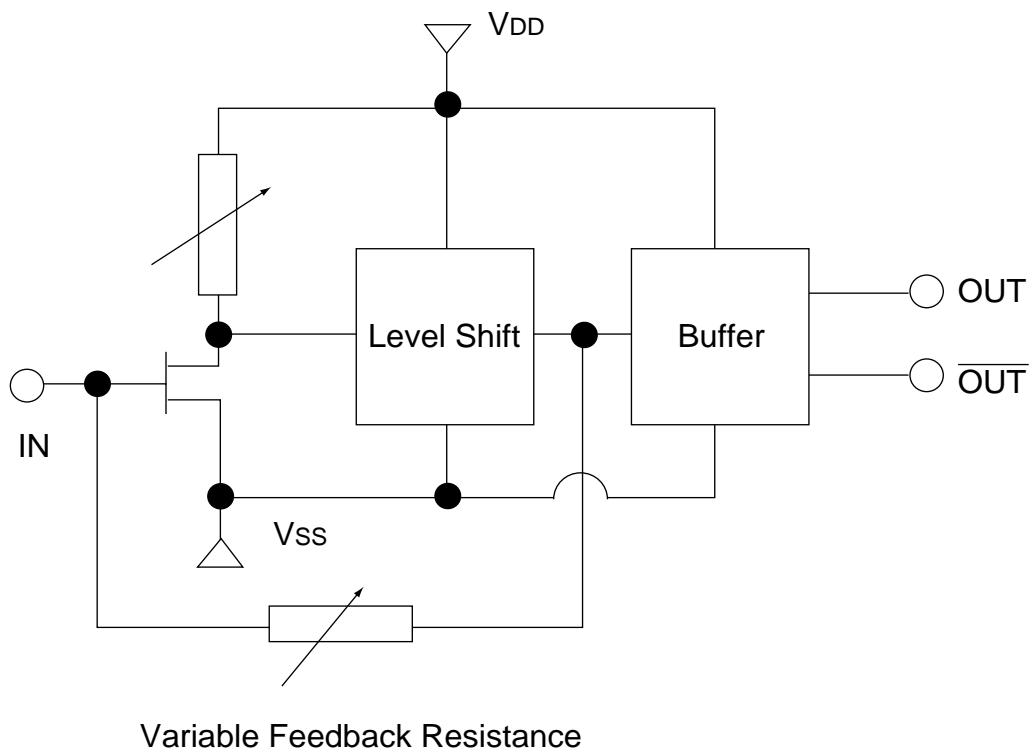
◆ Electrical Characteristics

$T_a=25^\circ\text{C}$, $V_{DD}=3.3\text{ V}$, $V_{SS}=\text{GND}$, unless specified

Parameter	Symbol	Test Conditions	Value			Units
			Min.	Typ.	Max.	
Supply Current	I_{DD}	DC	18	35	45	mA
Gain(Positive)	S_{21P}	PIN=-50dBm f=1MHz, RL=50Ω	27	28.5	32	dB
Gain(negative)	S_{21N}	PIN=-50dBm f=1MHz, RL=50Ω	27	28.5	32	dB
-3dB High Frequency Cut-off (positive)	F_{CP}	PIN=-50dBm RL=50Ω	265	340	600	MHz
-3dB High Frequency Cut-off (negative)	F_{CN}	PIN=-50dBm RL=50Ω	265	320	600	MHz
Input Impedance	R_I	f=1MHz	350	450	550	Ω
Trans-Impedance(positive)	Z_{TP}	*1, f=1MHz	4.5	6.5	-	KΩ
Trans-Impedance(negative)	Z_{TN}	*1, f=1MHz	4.5	6.5	-	KΩ
Output Voltage(positive)	V_{OP}	DC	1.5	2.4	2.9	V
Output Voltage(negative)	V_{ON}	DC	1.5	2.4	2.9	V
Input Voltage	V_I	DC	0.65	0.88	1.05	V

$$*1 Z_{TP,N} = \frac{(R_I+50)}{2} \times 10 \quad \frac{S_{21P,N}}{20}$$

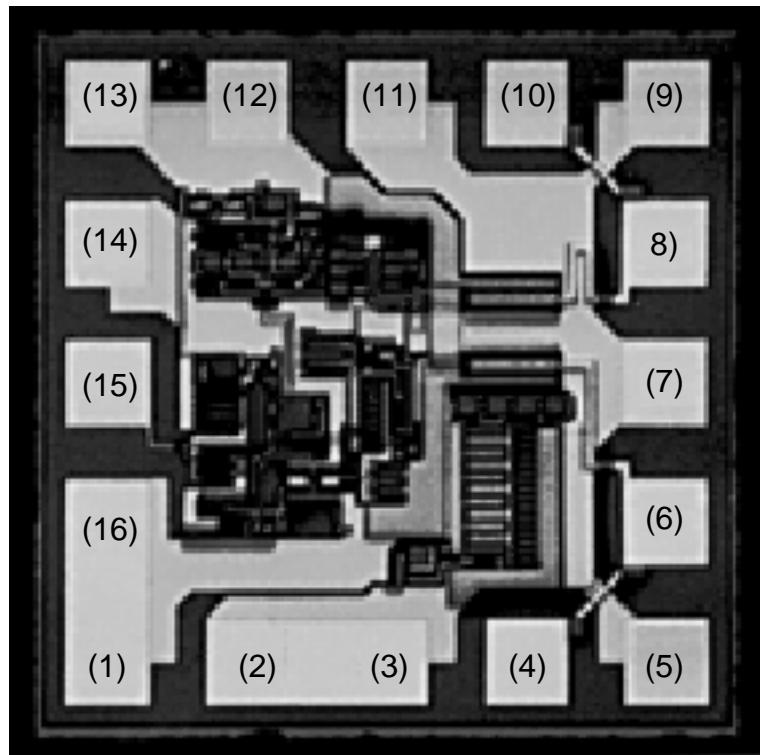
◆ *Block Diagram*



◆ *Die Pad Description*

V_{DD}	Supply Voltage
V_{SS}	Supply Voltage
IN	Input
OUT	Output
\overline{OUT}	Output

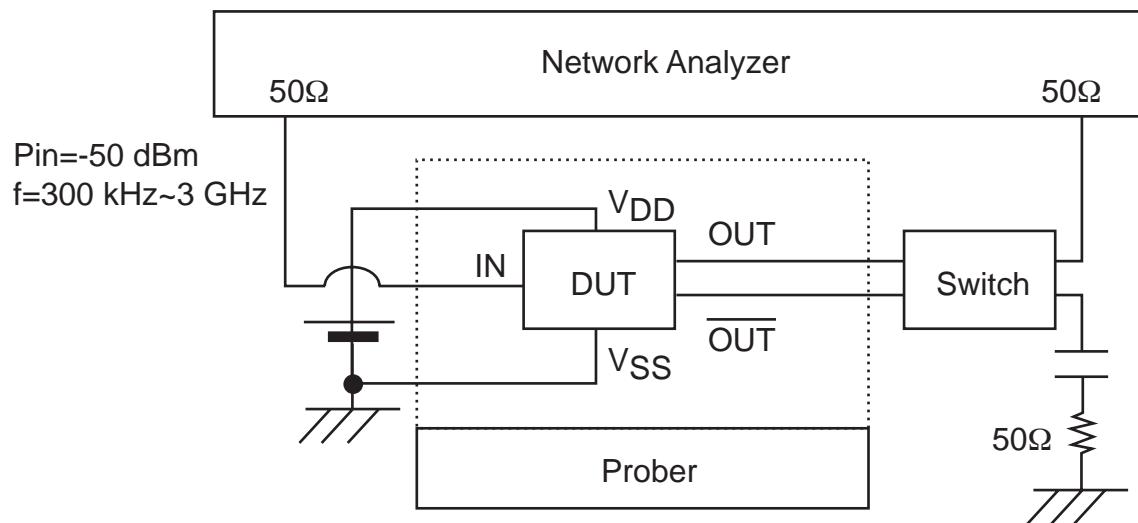
◆ Die Pad Assignments



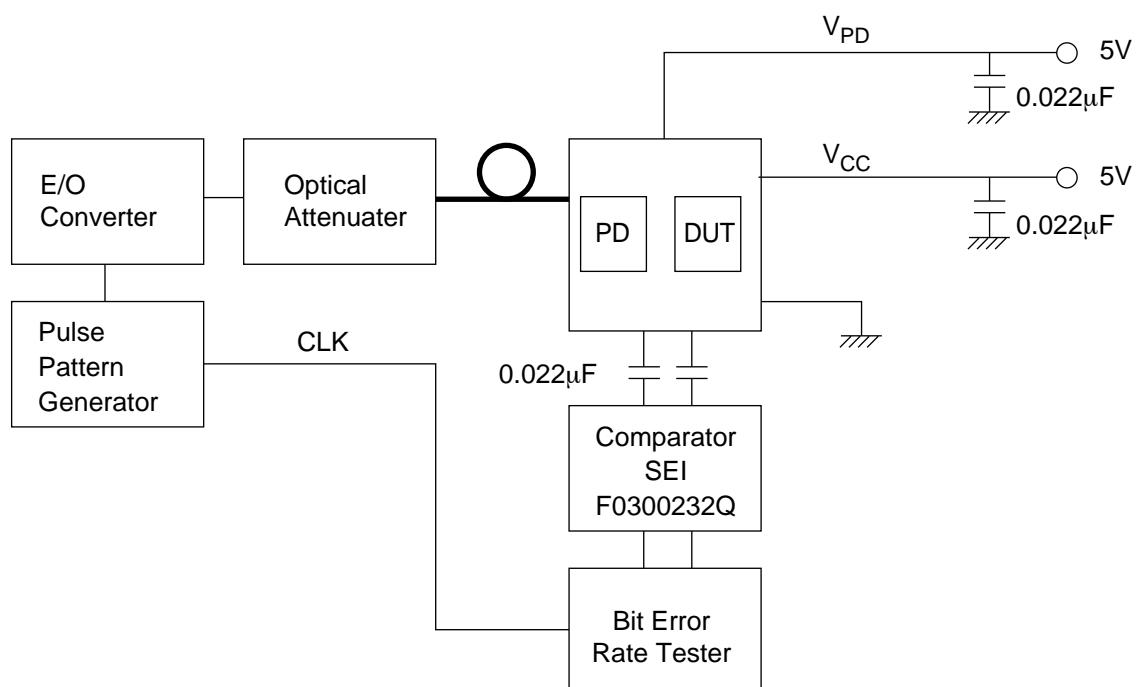
No.	Symbol	Center Coordinates(μm)	No.	Symbol	Center Coordinates(μm)
(1)	$V_{DD3.3}$	(75,75)	(10)	OUT	(555,715)
(2)	$V_{DD5.0}$	(235,75)	(11)	V_{ss}	(396,715)
(3)	$V_{DD5.0}$	(395,75)	(12)	$V_{DD3.3}$	(235,715)
(4)	\overline{OUT}	(555,75)	(13)	$V_{DD3.3}$	(75,715)
(5)	V_{ss}	(715,75)	(14)	V_{ss}	(75,555)
(6)	\overline{OUT}	(715,235)	(15)	IN	(75,395)
(7)	V_{ss}	(715,395)	(16)	$V_{DD3.3}$	(75,235)
(8)	OUT	(715,555)	O		(0,0)
(9)	V_{ss}	(715,715)	A		(790,790)

◆ Test Circuits

1) AC Characteristics



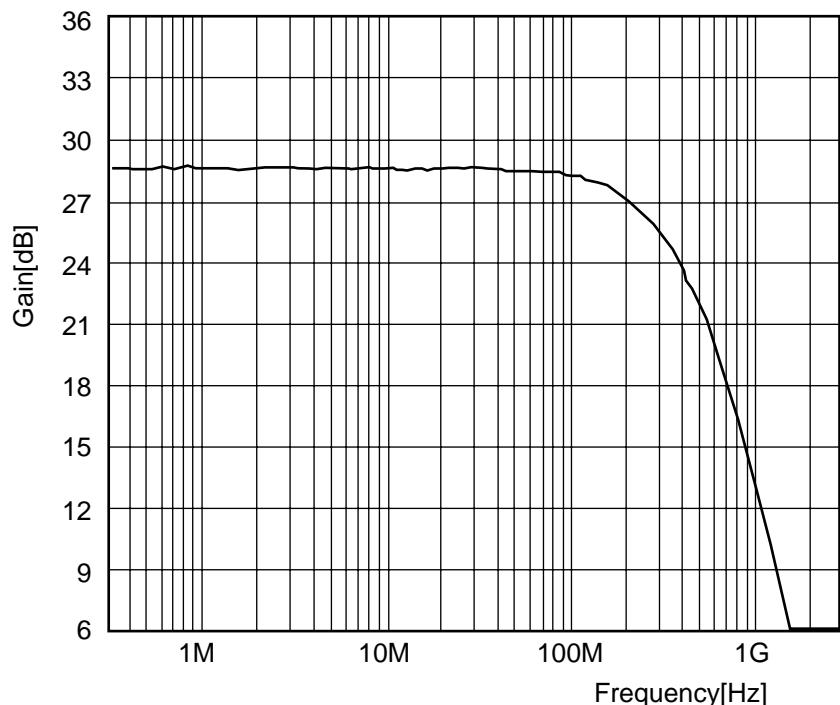
2) Sensitivity Characteristics



◆ **Examples of AC Characteristics**

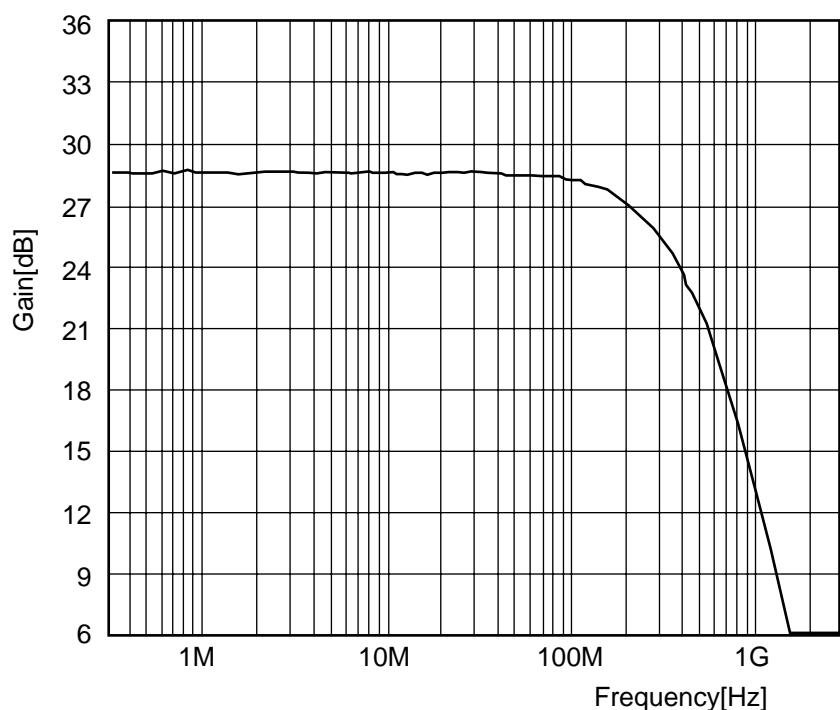
(1) Gain (S_{21P})

$T_a=25^\circ\text{C}$, $V_{DD}=+3.3\text{ V}$, $V_{SS}=\text{GND}$, $\text{Pin}=-50\text{ dBm}$, $\text{RL}=50\text{ }\Omega$, 300 kHz-3 GHz



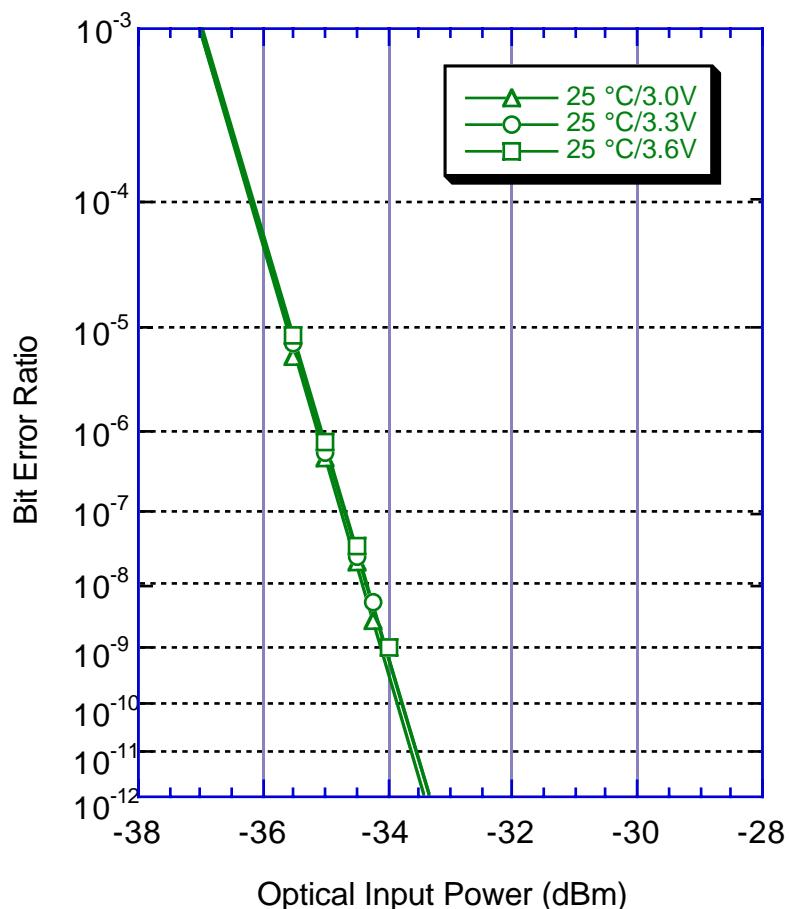
(2) Gain (S_{21N})

$T_a=25^\circ\text{C}$, $V_{DD}=+3.3\text{ V}$, $V_{SS}=\text{GND}$, $\text{Pin}=-50\text{ dBm}$, $\text{RL}=50\text{ }\Omega$, 300 kHz-3 GHz



(3) Input Noise Current Density & Transimpedance

INPUT NOISE CURRENT DENSITY & TRANSIMPEDANCE(Typical Values)		
Freq. (MHz)	Zt(Ω) (RF transimpedance)	Ini(pA/√Hz) (Equivalent input noise currentdensity)
10	8246	1.29
20	8281	1.35
30	8101	1.37
50	8263	1.44
80	8391	1.42
100	8120	1.23
200	7583	1.72
300	6884	2.42
400	5589	2.82
500	4016	3.27
600	2668	4.15
700	2006	4.55
800	1546	5.85
900	997	6.06
1000	697	8.02

◆ Typical Bit Error RatePRBS $2^{23}-1$, $T_a=25\text{ }^{\circ}\text{C}$, $V_{DD}=3.3\text{ V}$, $V_{SS}=\text{GND}$, $RL=50\text{ }\Omega$ 

◆ ***General Description***

A transimpedance amplifier is applied as a pre-amplifier which is an amplifier for a faint photo-current from a PIN photo diode (PD). The performance in terms of sensitivity, bandwidth, and so on, obtained by this transimpedance amplifier strongly depend on the capacitance brought at the input terminal; therefore, “typical”, “minimum”, or “maximum” parameter descriptions can not always be achieved according to the employed PD and package, the assembling design, and other technical experts. This is the major reason that there is no product lineup of packaged transimpedance amplifiers.

Thus, for optimum performance of the transimpedance amplifier, it is essential for customers to design the input capacitance carefully.

Hardness to electro-magnetic interference and fluctuation of a power supply voltage is also an important point of the design, because very faint photo-current flows into the transimpedance amplifier. Therefore, in the assembly design of the interconnection between a PD and a transimpedance, noise should be taken into consideration.

◆ ***Low Voltage Operation***

The F0100208B features a single 3.3 V supply operation, which is in great demand recently, because most of logic IC's operate with the supply voltage of 3.3 V. The analog IC's with a single 3.3 V supply for use in fiber optic communication systems are offered by only SEI.

◆ ***Recommendation***

SEI basically recommends the F08 series PINAMP modules for customers of the transimpedance amplifiers. In this module, a transimpedance amplifier, a PD, and a noise filter circuit are mounted on a TO-18-can package hermetically sealed by a lens cap, having typically a fiber pigtail. The F08 series lineups are the best choice for customers to using the F01 series transimpedance amplifiers. SEI's F08 series allows the customers to resolve troublesome design issues and to shorten the development lead time.

◆ ***Noise Performance***

The F0100208B based on GaAs FET's shows excellent low-noise characteristics compared with IC's based on the silicon bipolar process. Many transmission systems often

demand superior signal-to-noise ratio, that is, high sensitivity; the F0100208B is the best choice for such applications.

The differential circuit configuration in the output enable a complete differential operation to reduce common mode noise: simple single ended output operation is also available.

◆ ***Die-Chip Description***

The F0100208B is shipped like the die-chip described above. The die thickness is typically $280 \mu\text{m} \pm 20 \mu\text{m}$ with the available pad size uncovered by a passivation film of $95 \mu\text{m}$ square. The material of the pads is TiW/Pt/Au and the backside is metalized by Ti/Au.

◆ ***Assembling Condition***

SEI recommends the assembling process as shown below and affirms sufficient wire-pull and die-shear strength. The heating time of one minute at the temperature of 310°C gave satisfactory results for die-bonding with AuSn performs. The heating and ultrasonic wire-bonding at the temperature of 150°C by a ball-bonding machine is effective.

◆ ***Quality Assurance***

For the F01 series products, there is only one technically inevitable drawback in terms of quality assurance which is to be impossible of the burn-in test for screening owing to die-shipment. SEI will not ship them if customers do not agree on this point. On the other hand, the lot assurance test is performed completely without any problems according to SEI's authorized rules. A microscope inspection is conducted in conformance with the MIL-STD-883C Method 2010.7.

◆ ***Precautions***

Owing to their small dimensions, the GaAs FET's from which the F0100208B is designed are easily damaged or destroyed if subjected to large transient voltages. Such transients can be generated by power supplies when switched on if not properly decoupled. It is also possible to induce spikes from static-electricity-charged operations or ungrounded equipment.